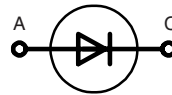
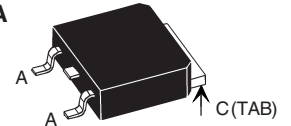


Power Schottky Rectifier

$$\begin{aligned} I_{FAV} &= 6 \text{ A} \\ V_{RRM} &= 150 \text{ V} \\ V_F &= 0.62 \text{ V} \end{aligned}$$

V_{RSM} V	V_{RRM} V	Type	marking on product
150	150	DSS 6-015AS	6Y150AS


TO-252 AA


A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}	$T_C = 160^\circ\text{C}$; rectangular, $d = 0.5$	20	A
I_{FAV}		6	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	80	A
E_{AS}	$I_{AS} = 1 \text{ A}$; $L = 100 \mu\text{H}$; $T_{VJ} = 25^\circ\text{C}$; non repetitive	0.05	mJ
I_{AR}	$V_A = 1.5 \cdot V_{RRM}$ typ.; $f = 10 \text{ kHz}$; repetitive	0.1	A
$(dv/dt)_{cr}$		18	kV/ μs
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{VJM}		175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	50	W
Weight	typical	0.3	g

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM} -values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	0.3 2.5	mA mA
V_F	$I_F = 6 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$ $I_F = 6 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$ $I_F = 12 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	0.62 0.78 0.71	V V V
R_{thJC}		3.0	K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

Dimensions see Outlines.pdf

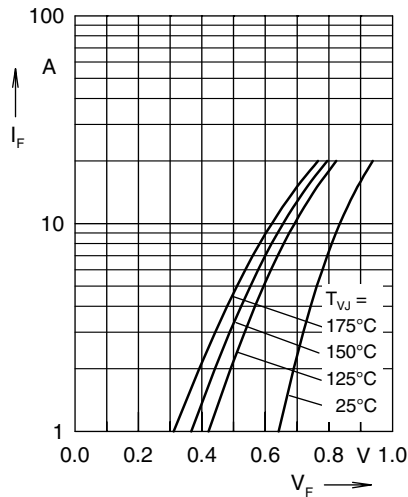


Fig. 1 Maximum forward voltage drop characteristics

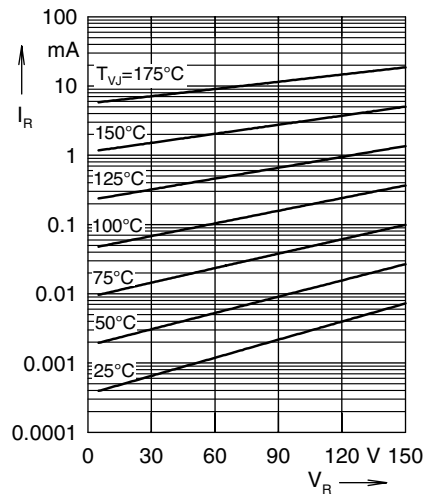


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

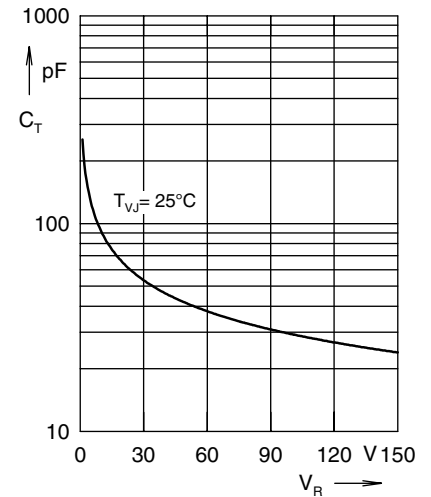


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

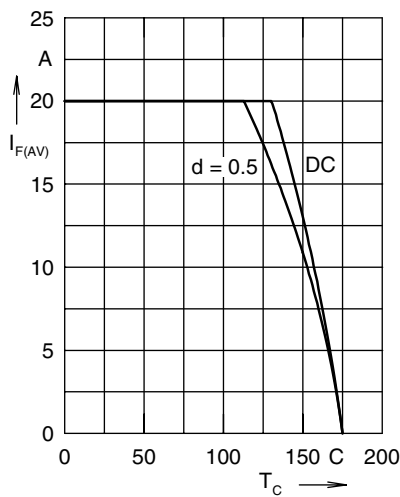


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

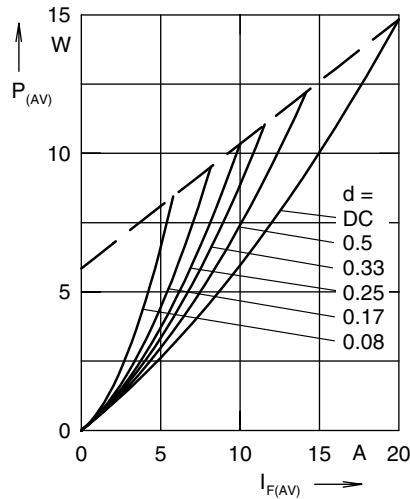


Fig. 5 Forward power loss characteristics

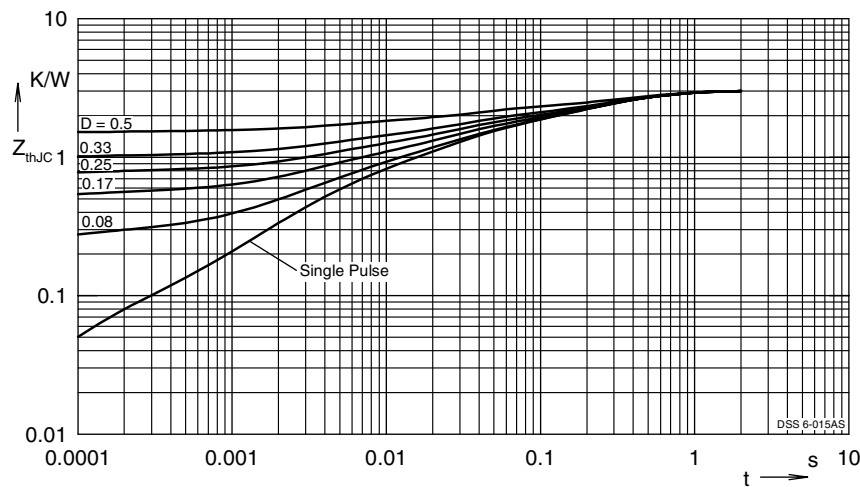


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode